



Docket No. 204552030500  
(PATENT)

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Patent Application of:  
Hidenori KAWANISHI et al.

Application No. 10/695,415.

Confirmation No. 5623

Filed: October 29, 2003

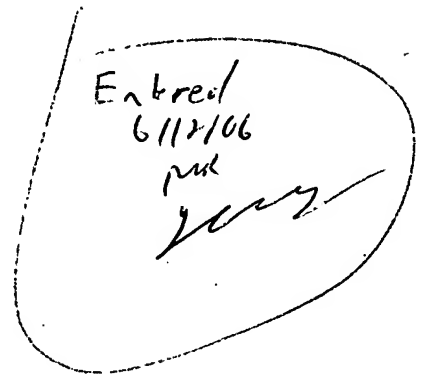
Art Unit: 2828

For: SEMICONDUCTOR LASER DEVICE  
MANUFACTURING METHOD THEREOF,  
AND OPTICAL DISK REPRODUCING AND  
RECORDING UNIT

Examiner: Tod T. Van Roy

**RESPONSE UNDER 37 CFR 1.116**

MS AF  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450



Sir:

In response to the final Office Action dated February 13, 2006, please reconsider this application in light of the following remarks.

**REMARKS**

Claims 1-5, 10-15 and 20-26 stand rejected under 35 USC 103(a) on Nomura (JP 2000-340894) in view of Fukunaga (EP 0 920 096). Applicants respectfully traverse this rejection.

Claim 1 recites a quantum well active layer made of a non-Al based material and comprising barrier layers and well layers alternately stacked in such a way that the top and bottom layers of the quantum well active layer are barrier layers, wherein the quantum well active layer is doped with a second conductivity type of impurity. The Examiner has conceded that Nomura does not disclose